N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
30	0.057 at V_{GS} = 10 V	5.6[a]	5.5
	0.082 at V_{GS} = 4.5 V	4.7	

FEATURES

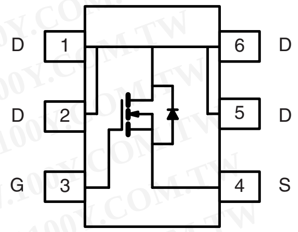
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

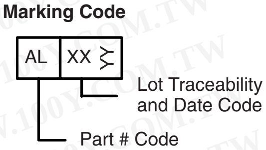
- Load Switch for Portable Devices

SOT-363
SC-70 (6-LEADS)



Top View

Marking Code



Ordering Information: Si1472DH-T1-E3 (Lead (Pb-free)
Si1472DH-T1-GE3 (Lead (Pb-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)[a]	T_C = 25 °C	I_D	5.6	A
	T_C = 70 °C		4.5	
	T_A = 25 °C		4.2[b, c]	
	T_A = 70 °C		3.4[b, c]	
Pulsed Drain Current		I_{DM}	15	
Avalanche Current	L = 0.1 mH	I_{AS}	10	
Repetitive Avalanche Energy		E_{AS}	5	mJ
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	2.3	A
	T_A = 25 °C		1.3[b, c]	
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	2.8	W
	T_C = 70 °C		1.8	
	T_A = 25 °C		1.5[b, c]	
	T_A = 70 °C		1.0[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[b, d]	t ≤ 5 s	R_{thJA}	60	80	°C/W
Maximum Junction-to-Foot (Drain)	Steady	R_{thJF}	34	45	

Notes:
a. Based on T_C = 25 °C.
b. Surface Mounted on 1" x 1" FR4 board.
c. t = 5 s.
d. Maximum under steady state conditions is 125 °C/W.

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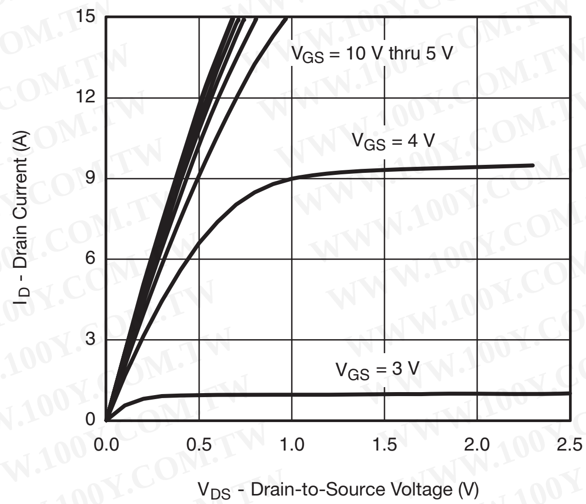
SPECIFICATIONS T_J = 25 °C, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		25.15		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I_D = 250 µA		5.6		mV/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1		3	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			1	nA
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 85 °C			10	µA
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = ≥ 5 V, V_{GS} = 10 V	15			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 4.2 A		0.046	0.057	Ω
		V_{GS} = 4.5 V, I_D = 3.5 A		0.065	0.082	Ω
Forward Transconductance	g_{fs}	V_{DS} = 15 V, I_D = 4.2 A		8.5		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		380		pF
Output Capacitance	C_{oss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		75		pF
Reverse Transfer Capacitance	C_{rss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		45		pF
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 4.2 A		7	11	nC
		V_{DS} = 24V, V_{GS} = 4.5 V, I_D = 4.2 A		3.3	5	nC
Gate-Source Charge	Q_{gs}	V_{DS} = 24V, V_{GS} = 4.5 V, I_D = 4.2 A		1.2		nC
Gate-Drain Charge	Q_{gd}	V_{DS} = 24V, V_{GS} = 4.5 V, I_D = 4.2 A		1.0		nC
Gate Resistance	R_g	f = 1 MHz		7.1	10.6	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 4.4 Ω, $I_D \cong$ 3.4 A, V_{GEN} = 10 V, R_g = 1 Ω		7.0	11	ns
Rise Time	t_r	V_{DD} = 15 V, R_L = 4.4 Ω, $I_D \cong$ 3.4 A, V_{GEN} = 10 V, R_g = 1 Ω		56	84	ns
Turn-Off DelayTime	$t_{d(off)}$	V_{DD} = 15 V, R_L = 4.4 Ω, $I_D \cong$ 3.4 A, V_{GEN} = 10 V, R_g = 1 Ω		18	27	ns
Fall Time	t_f	V_{DD} = 15 V, R_L = 4.4 Ω, $I_D \cong$ 3.4 A, V_{GEN} = 10 V, R_g = 1 Ω		5.5	9	ns
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 5.4 Ω, $I_D \cong$ 2.8 A, V_{GEN} = 4.5 V, R_g = 1 Ω		15	23	ns
Rise Time	t_r	V_{DD} = 15 V, R_L = 5.4 Ω, $I_D \cong$ 2.8 A, V_{GEN} = 4.5 V, R_g = 1 Ω		95	143	ns
Turn-Off DelayTime	$t_{d(off)}$	V_{DD} = 15 V, R_L = 5.4 Ω, $I_D \cong$ 2.8 A, V_{GEN} = 4.5 V, R_g = 1 Ω		12	18	ns
Fall Time	t_f	V_{DD} = 15 V, R_L = 5.4 Ω, $I_D \cong$ 2.8 A, V_{GEN} = 4.5 V, R_g = 1 Ω		7	11	ns
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I_S	T_C = 25 °C			2.3	A
Pulse Diode Forward Current[a]	I_{SM}				15	A
Body Diode Voltage	V_{SD}	I_S = 1.8 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 2.3 A, dI/dt = 100 A/µs		12.3	19	nC
Body Diode Reverse Recovery Charge	Q_{rr}	I_F = 2.3 A, dI/dt = 100 A/µs		5	7.5	ns
Reverse Recovery Fall Time	t_a	I_F = 2.3 A, dI/dt = 100 A/µs		7.6		ns
Reverse Recovery Rise Time	t_b	I_F = 2.3 A, dI/dt = 100 A/µs		4.7		ns

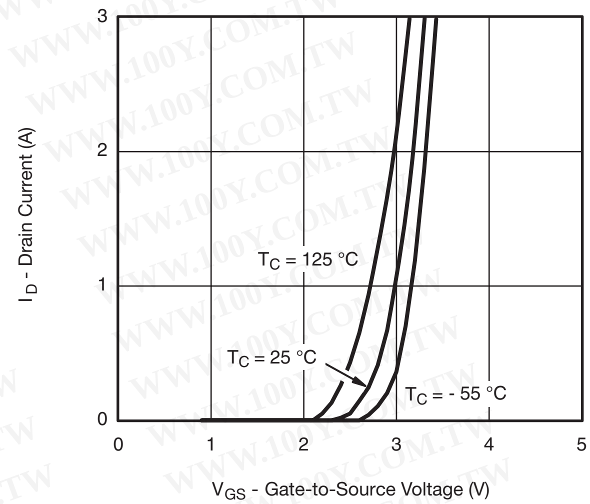
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

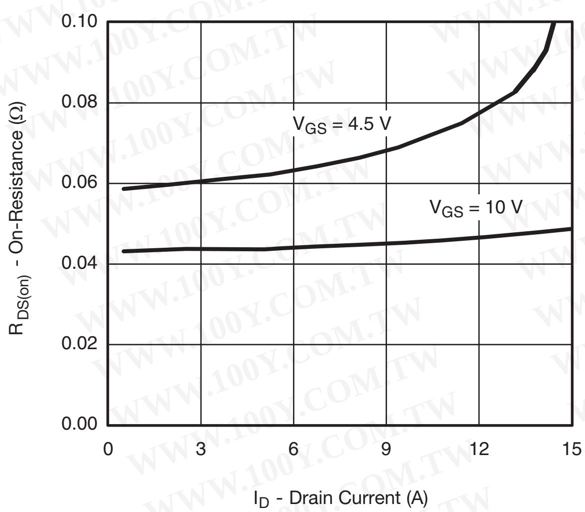
TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



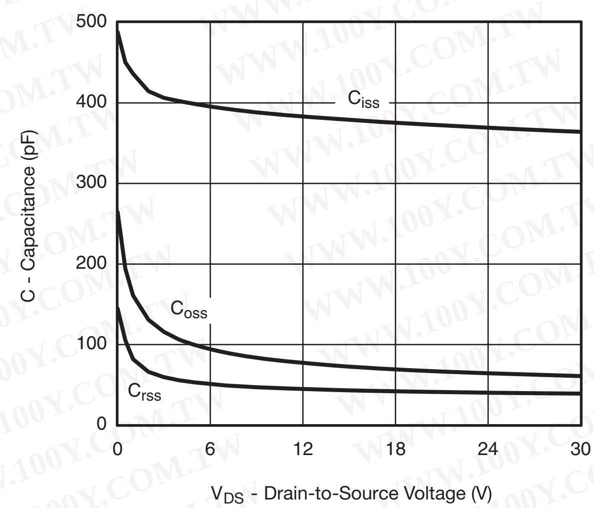
Output Characteristics



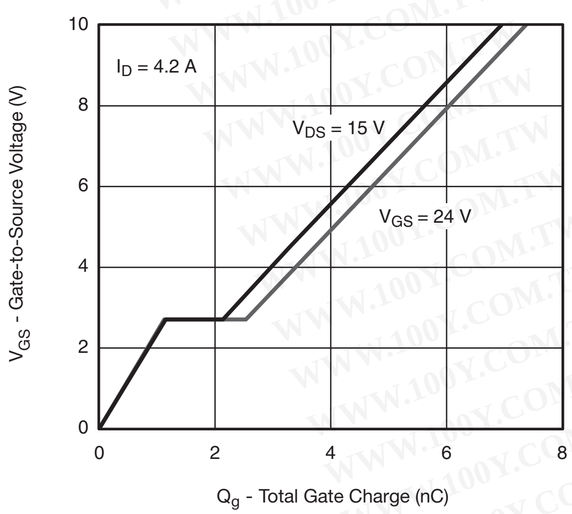
Transfer Characteristics Curves vs. Temperature



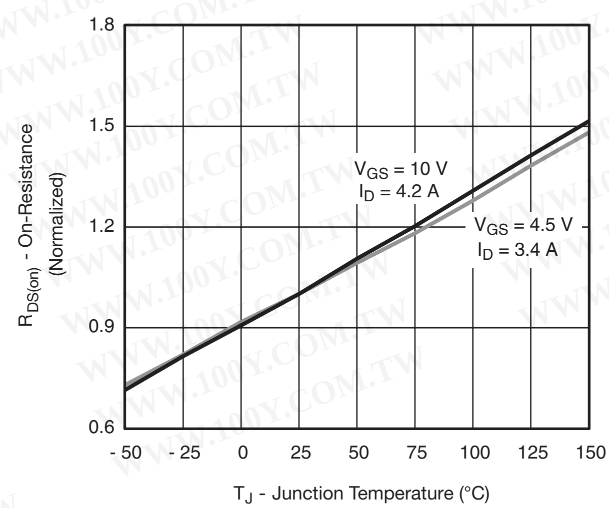
On-Resistance vs. Drain Current



Capacitance

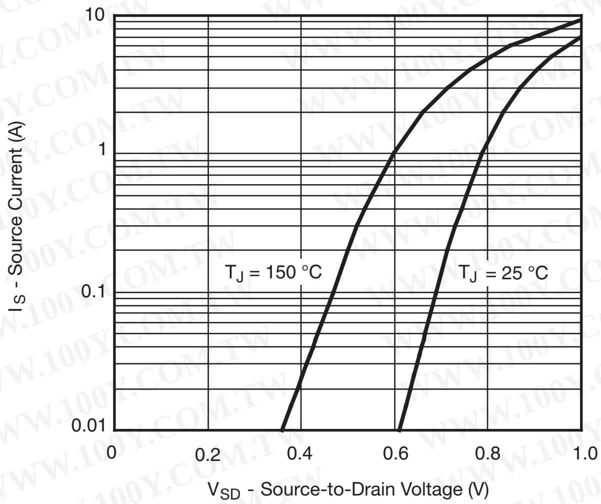


Gate Charge

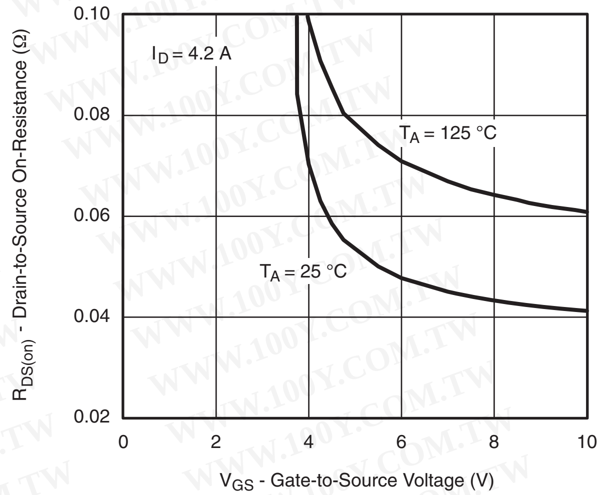


On-Resistance vs. Junction Temperature

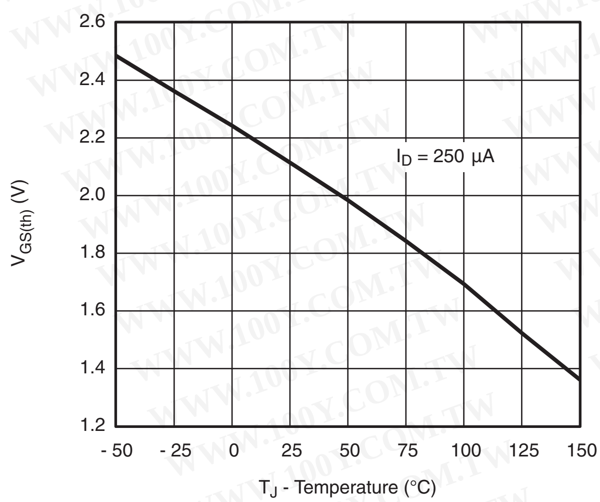
TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



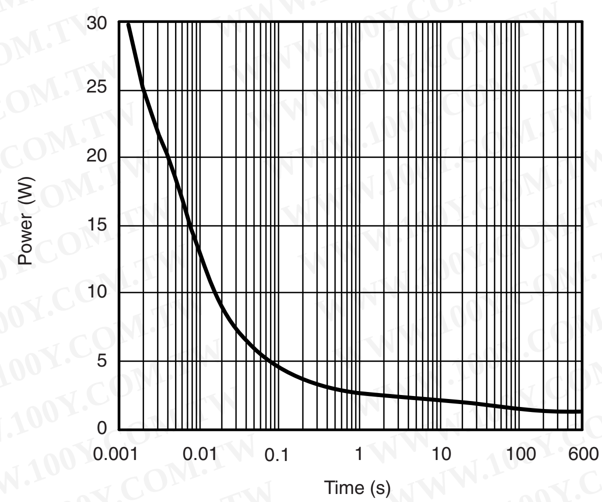
Source-Drain Diode Forward Voltage



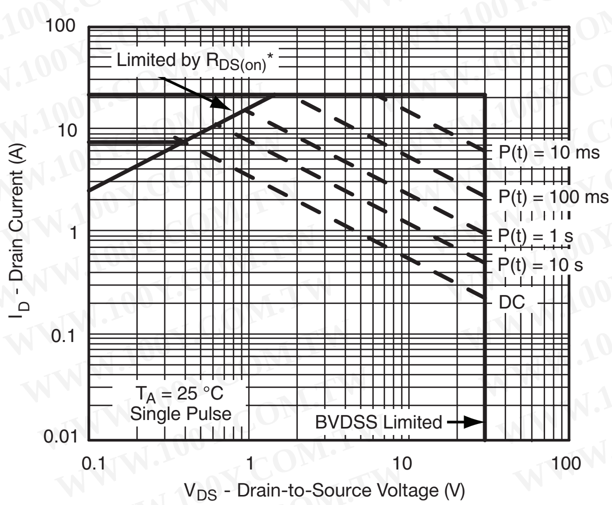
$R_{DS(on)}$ vs. V_{GS} vs. Temperature



Threshold Voltage



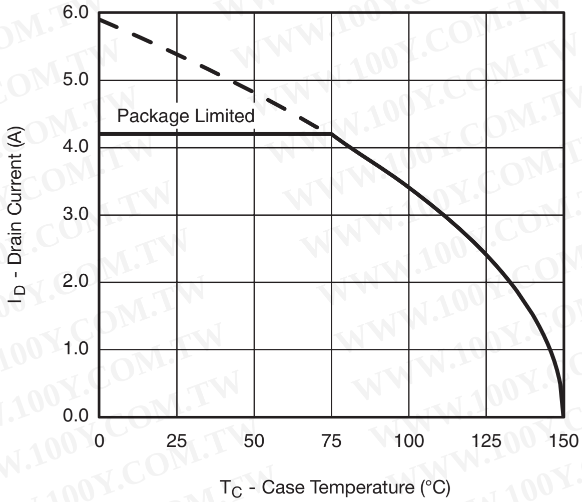
Single Pulse Power



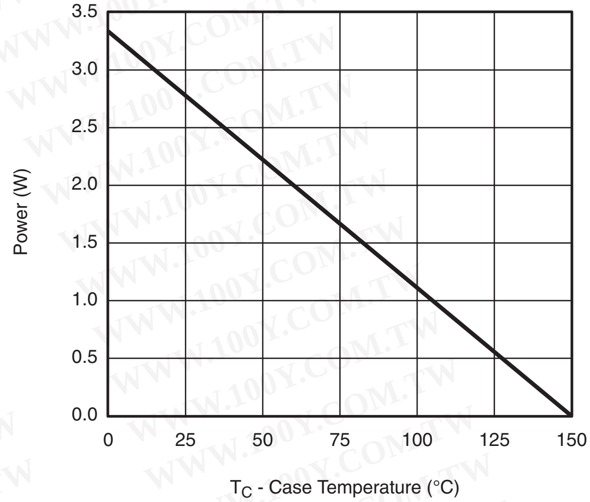
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



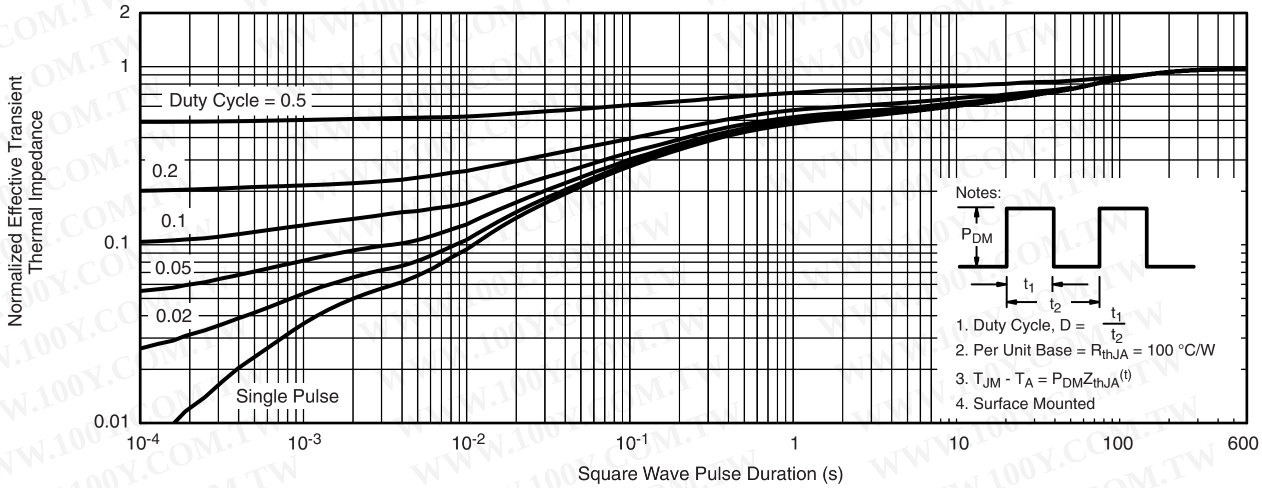
Current Derating*



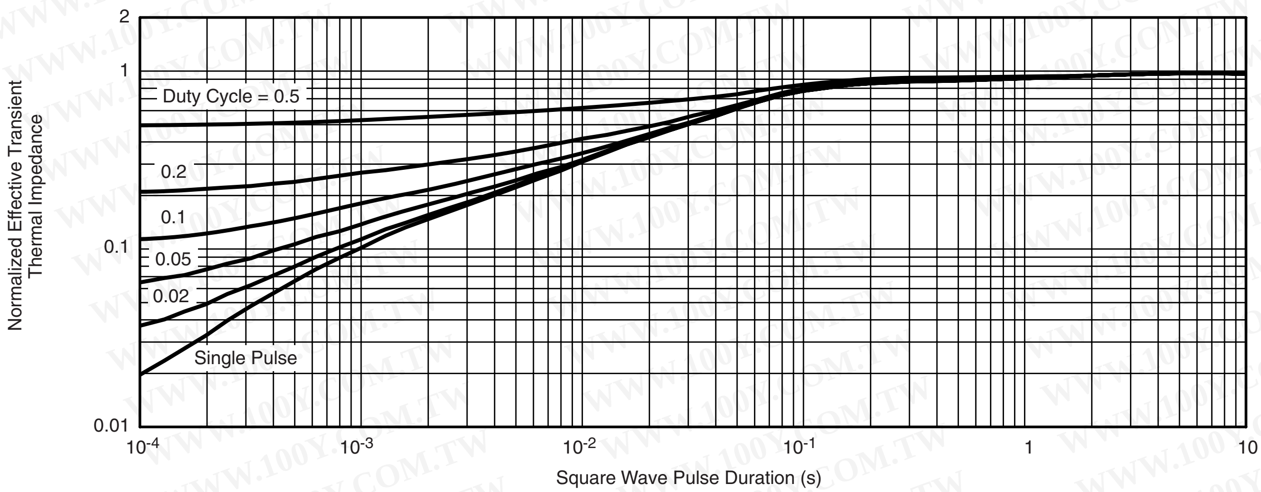
Power Derating

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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